

PATENT APPLICATION

Sheet 1 of 2

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE
STATEMENT

(Use several sheets if necessary)

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Daniel R. Marshall		
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REFERENCE DESIGNATION

Rev 10,00 (PTO1449)

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NA ME	CLASS	SUB CLASS
Jul	1A	4,427,886	1/1984	Martin et al.	250	310
in	1B	4,534,016	8/1985	Kirkpatrick et al.	365	128
200	1C	4,600,839	7/1986	Ichihashi et al.	250	310
are	1D	4,760,567	7/1988	Crewe	369	101
Jup	1E	5,402,410	3/1995	Yoshimura et al.	369	275.1
صد	1F	5,557,596	9/1996	Gibson et al.	369	101
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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	NAME		SUB CLASS	TRANSLATION	
				CLASS		YES	NO
1L							
1M					_		
1N							
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1P							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

Jup	1Q	E. Huber et al., "Laser Induced Crystallization of Amorphous GeTe: A Time Resolved Study," Physics Review B, Vol. 36, No. 3, pp. 1595-1604 (July 15, 1987).					
AUC.	1R	R.T. Howe et al., "Silicon Micromechanics: Sensors and Actuators on a Chip," IEEE Spectrum, pp. 29-35 (July 1990).					
)MP	18	V.P. Jaecklin et al., "Novel Polysilicon Comb Actuators for XY-Stages", Proceedings of Micro Electro Mechanical Systems," pp. 147-149 (February 1992).					
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PATENT APPLICATION

Sheet 2 of 2

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FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT				ATTY, DOCKET NO.	ľ	SERIALN	Ю.		
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	2Q	G.W. Jones et al., "Silicon Field Emission Transistors and Diodes," IEEE Trans. on Components,							
ماد		Hybrids and Manufacturing Technology, Vol. 15, No. 6, pp. 1051-1055 (December 1992).							
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SIMP	2R	C.A. Spindt et al. Cones," Journal o	, "Physical Properties of of Applied Physics, Vol	of Thin-Film Field Emission C . 47, No. 12, pp. 5248-5263	athodes w 3 (Decemb	ith Molyl er 1976)	bdenur I.	n	
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)M		Device, Applied Physics Letters, Vol. 44, No. 7, pp. 695-697 (April 1984).							
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